

Specification MOS/CV2384	<u>SECURITY</u>	
Issue 3 Dated 20th July 1959	<u>Specification</u>	<u>Valve</u>
To be read in conjunction with K1001	UNCLASSIFIED	UNCLASSIFIED

Indicates a change ←

TYPE OF VALVE - Silicon Junction diode		<u>MARKING</u> C.V. Number Polarity marking and where practicable factory and date code. See K1001/4	
<u>RATINGS</u> <u>ALL LIMITING VALUES ARE ABSOLUTE</u>		<u>DIMENSIONS</u> See specification CV 4073	
Max. Reverse Working Voltage	(V)	60	Note
Max. Dissipation at temperature up to 75°C	(mW)	150	
Max. Dissipation at 100°C	(mW)	100	
Max. Forward D.C. Current at 25°C	(mA)	100	
Max. Forward D.C. Current at 100°C	(mA)	60	
Max. rectified A.C. Current at 25°C	(mA)	80	A
Max. rectified A.C. Current at 100°C	(mA)	45	A
Max. reverse current at 25°C	(μ A)	0.1	B
Max. reverse current at 100°C	(μ A)	10	B
Max. Ambient Temperature rating -40°C to + 150°C			C
<u>CAPACITANCE</u> (pF)			
Cak (max)		5	
		<u>MOUNTING POSITION</u> Any	

NOTES

A. Mean rectified current from 50 c/s A.C. 60 volt peak into a resistive or inductive load.

B. Applied voltage - 60V

C. At ambient temperature in excess of 75°C the ratings for dissipation, forward D.C. current and rectified A.C. current decrease linearly with temperature, reducing to zero in each case at an ambient of 150°C.

TESTS

For all purposes the tests specified in the current specification MOS/CV4073 shall apply.